



DECLARATION FOR PATENT APPLICATION

(03S1247)

As a below named inventor, I declare that my residence, mailing address and citizenship are as stated below by my name; I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

SEMICONDUCTOR MEMORY INCLUDING STATIC RANDOM ACCESS MEMORY FORMED OF FINFET

the specification of which (check applicable box(es))

☐ is attached hereto.

☒ was filed on March 18, 2004 as United States Application No. 10/802,799
or PCT International Application No.

☐ and was amended on

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56.

I hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 35 U.S.C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:

Country	Category	Application Number	Filing Date	Priority Claim
Japan	Patent	2003-375851	November 5, 2003	Yes

I hereby appoint as my attorneys, with full power of substitution and revocation, to prosecute this application and transact all business in the Patent and Trademark Office connected therewith: the practitioners at:

Customer Number : 22850

of Oblon, Spivak, McClelland, Maier & Neustadt, P.C.. Please address all correspondence and telephone communications to the address and telephone number for this Customer Number.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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(03S1247)

I declare further that my citizenship, residence and mailing address are as stated below next to my name:

[1st Inventor]

Residence Address: Yokohama-shi, Japan

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Takeshi Watanabe

Takeshi Watanabe

APR. 14. 2004

Date:

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Kazunari Ishimaru

Kazunari Ishimaru

APR. 14. 2004

Date: